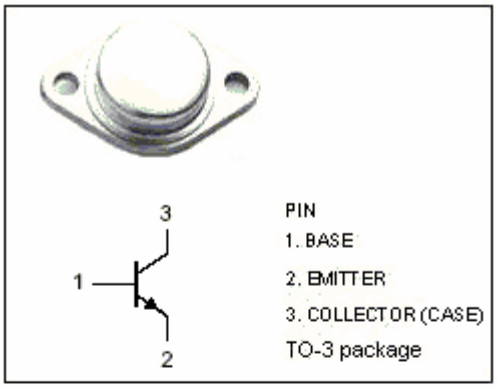
isc Silicon NPN Power Transistor BU111

DESCRIPTION

- Collector-Emitter Sustaining Voltag-
  : $V_{CEO(SUS)}$= 300V(Min)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= 1.5V(Max)@ I_C= 2.5A

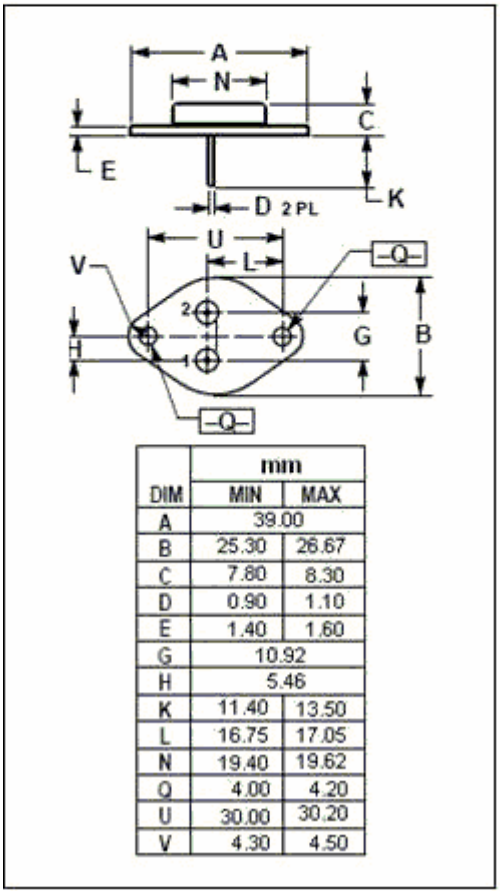


APPLICATIONS

- Designed for use in color TV receivers chopper supplies.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Peak Repetitive	8	A
I_B	Base Current	3	A
P_C	Collector Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

isc Silicon NPN Power Transistor BU111

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 100mA ;I_B= 0	200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA ;I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			1.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 400V; I_E=0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0			0.1	mA
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A ; V_{CE}= 10V		10		MHz